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(54) **SEMICONDUCTOR MODULE AND BOOST RECTIFIER CIRCUIT**

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See application file for complete search history.

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(56) **References Cited**

U.S. PATENT DOCUMENTS

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5,216,353	A *	6/1993	Mori	323/266
5,258,701	A *	11/1993	Pizzi et al.	323/269
6,456,509	B1	9/2002	Yasumura	
6,617,832	B1 *	9/2003	Kobayashi	323/266
7,019,501	B2	3/2006	Dogome et al.	
7,560,915	B2 *	7/2009	Ito et al.	323/266
7,872,454	B2	1/2011	Sutargja	

(Continued)

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FOREIGN PATENT DOCUMENTS

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CN	102437718	A	5/2012
JP	H05-060188	U	8/1993

(Continued)

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OTHER PUBLICATIONS

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CPC ..... **H02M 3/04** (2013.01); **H02M 1/08** (2013.01); **H02M 1/4225** (2013.01); **H01L 2924/181** (2013.01); **H03K 2217/0081** (2013.01); **Y02B 70/126** (2013.01)

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(57)

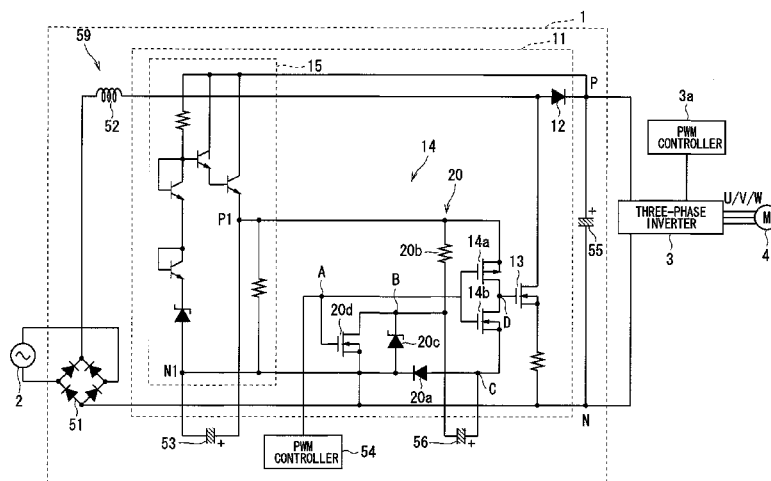
**ABSTRACT**

A semiconductor module includes a voltage generator, and a heat dissipating mechanism composed of, for example, an insulating heat dissipating sheet and a heat sink. The voltage generator is capable of generating, by using a built-in linear regulator function, a power source voltage to drive a boost converter based on a voltage boosted by the boost converter. The voltage generator is mounted on the heat dissipating mechanism.

(58) **Field of Classification Search**

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**5 Claims, 7 Drawing Sheets**



(56)

**References Cited**

**U.S. PATENT DOCUMENTS**

8,299,763	B2	10/2012	Sutardja	
8,686,761	B2	4/2014	Ozawa	
8,704,503	B2 *	4/2014	Williams	..... H02M 1/32 323/222
8,836,299	B2 *	9/2014	Tai	..... H02M 3/1588 323/222
2002/0044469	A1	4/2002	Yasumura	
2005/0040800	A1	2/2005	Sutardja	
2005/0258891	A1	11/2005	Ito et al.	
2007/0063678	A1	3/2007	Yoshikawa	
2008/0122417	A1	5/2008	Ng et al.	
2009/0167368	A1 *	7/2009	Chan et al.	..... 327/108
2010/0277141	A1	11/2010	Sutardja	
2011/0080118	A1 *	4/2011	Daniel	..... 315/297
2011/0228564	A1	9/2011	Urano et al.	
2012/0075890	A1	3/2012	Ozawa	
2013/0002224	A1	1/2013	Lin	

**FOREIGN PATENT DOCUMENTS**

JP	2002-064980	A	2/2002
JP	2005-168277	A	6/2005
JP	2006-053803	A	2/2006
JP	2010-088272	A	4/2010
JP	2011-193705	A	9/2011

JP	2012-074829	A	4/2012
KR	10-2006-0047875	A	5/2006
KR	2012-0098029	A	9/2012

**OTHER PUBLICATIONS**

An Office Action issued by the Korean Patent Office on Feb. 17, 2016, which corresponds to Korean Patent Application No. 10-2014-0019395 and is related to U.S. Appl. No. 14/145,324; with English language partial translation.

The First Office Action issued by the Patent Office of the People's Republic of China on Dec. 15, 2015, which corresponds to Chinese Patent Application No. 201410077138.1 and is related to U.S. Appl. No. 14/145,324; with English language partial translation.

An Office Action; Notice of Reason for Rejection, issued by the Japanese Patent Office on Jun. 14, 2016, which corresponds to Japanese Patent Application No. 2013-041643 and is related to U.S. Appl. No. 14/145,324; with English language partial translation.

The Second Office Action issued by the Patent Office of the People's Republic of China on Jul. 22, 2016, which corresponds to Chinese Patent Application No. 201410077138.1 and is related to U.S. Appl. No. 14/145,324; with English language partial translation.

An Office Action issued by the Korean Patent Office on Aug. 24, 2016, which corresponds to Korean Patent Application No. 10-2014-0019395 and is related to U.S. Appl. No. 14/145,324; with English language partial translation.

\* cited by examiner

FIG. 1

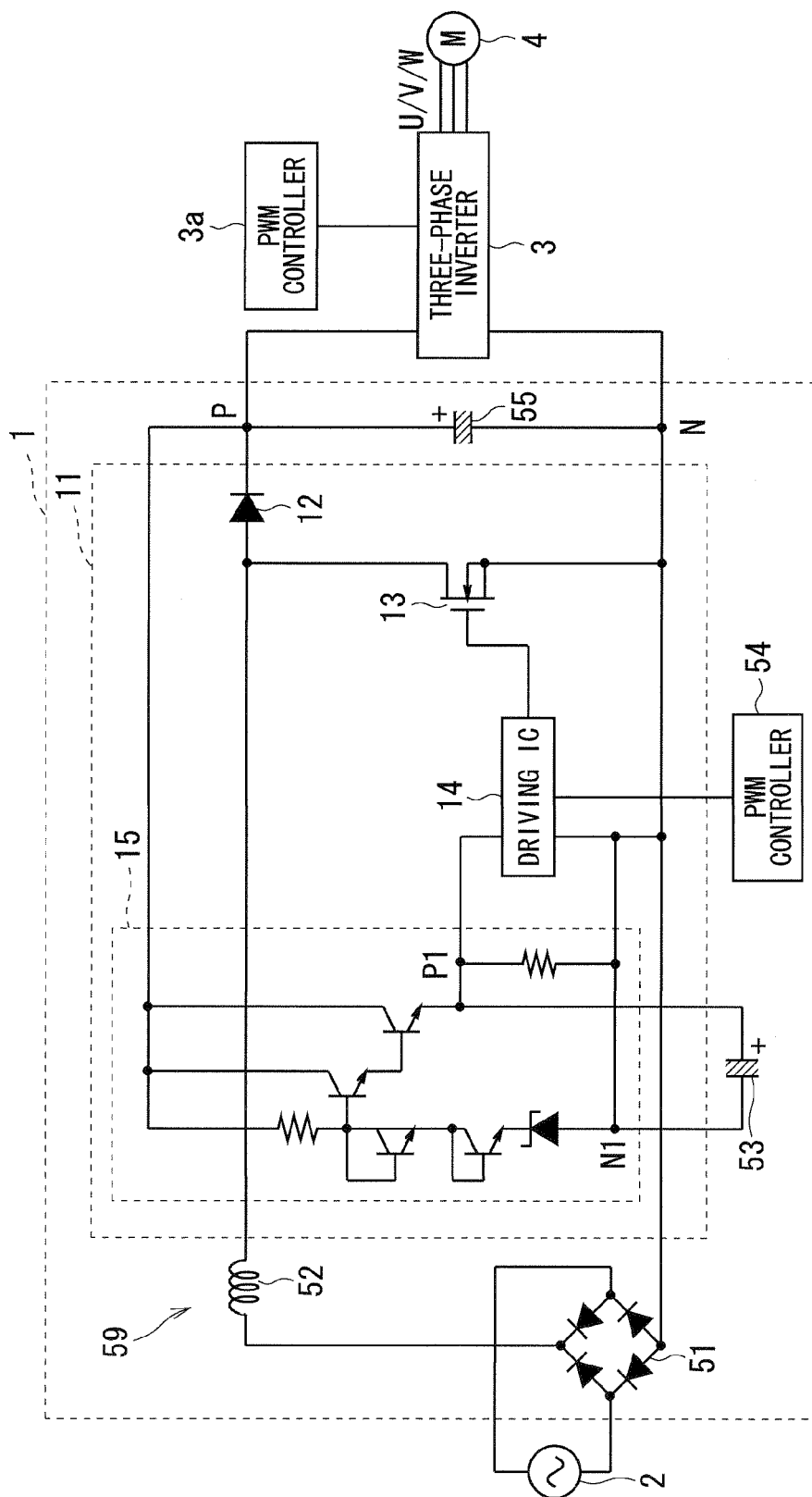


FIG. 2

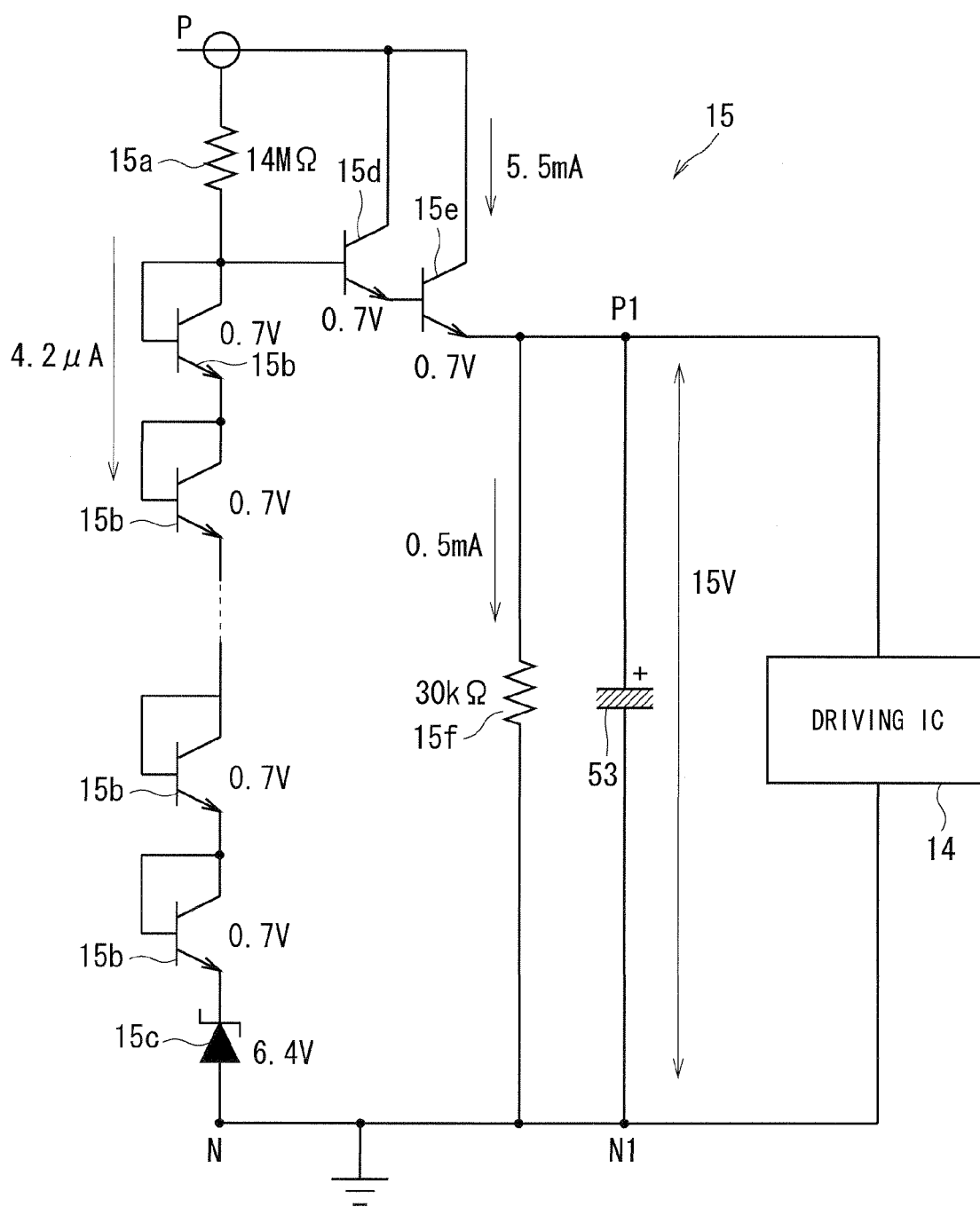
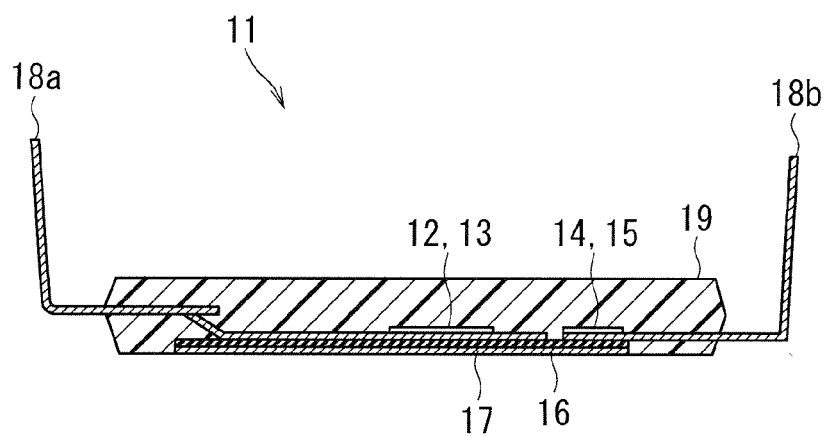
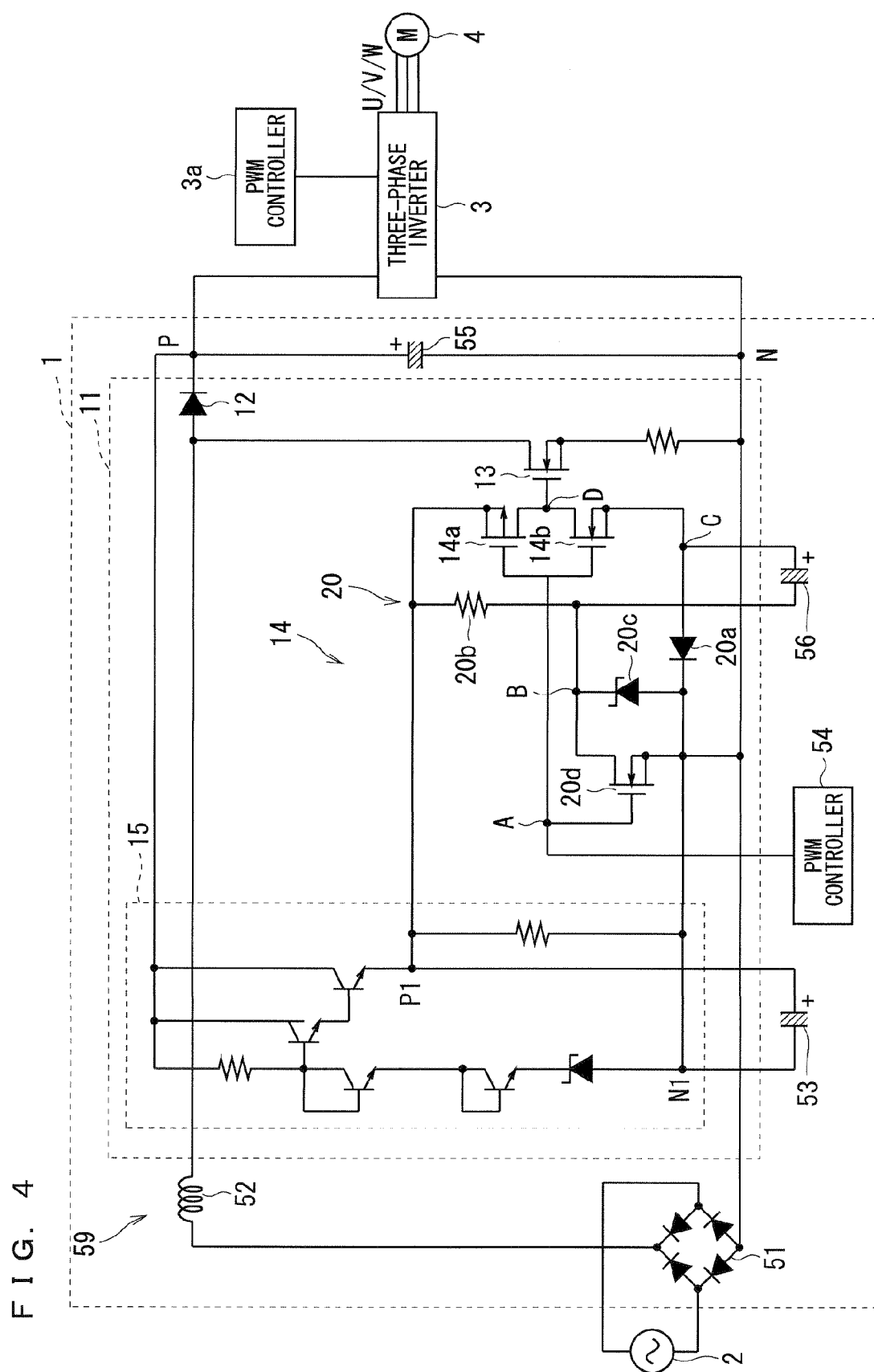
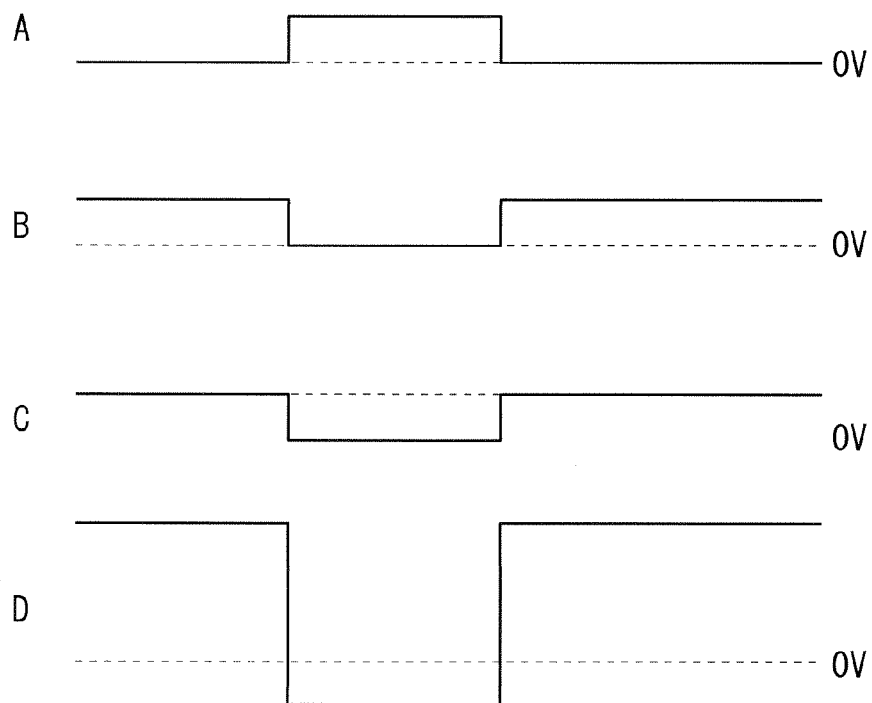


FIG. 3





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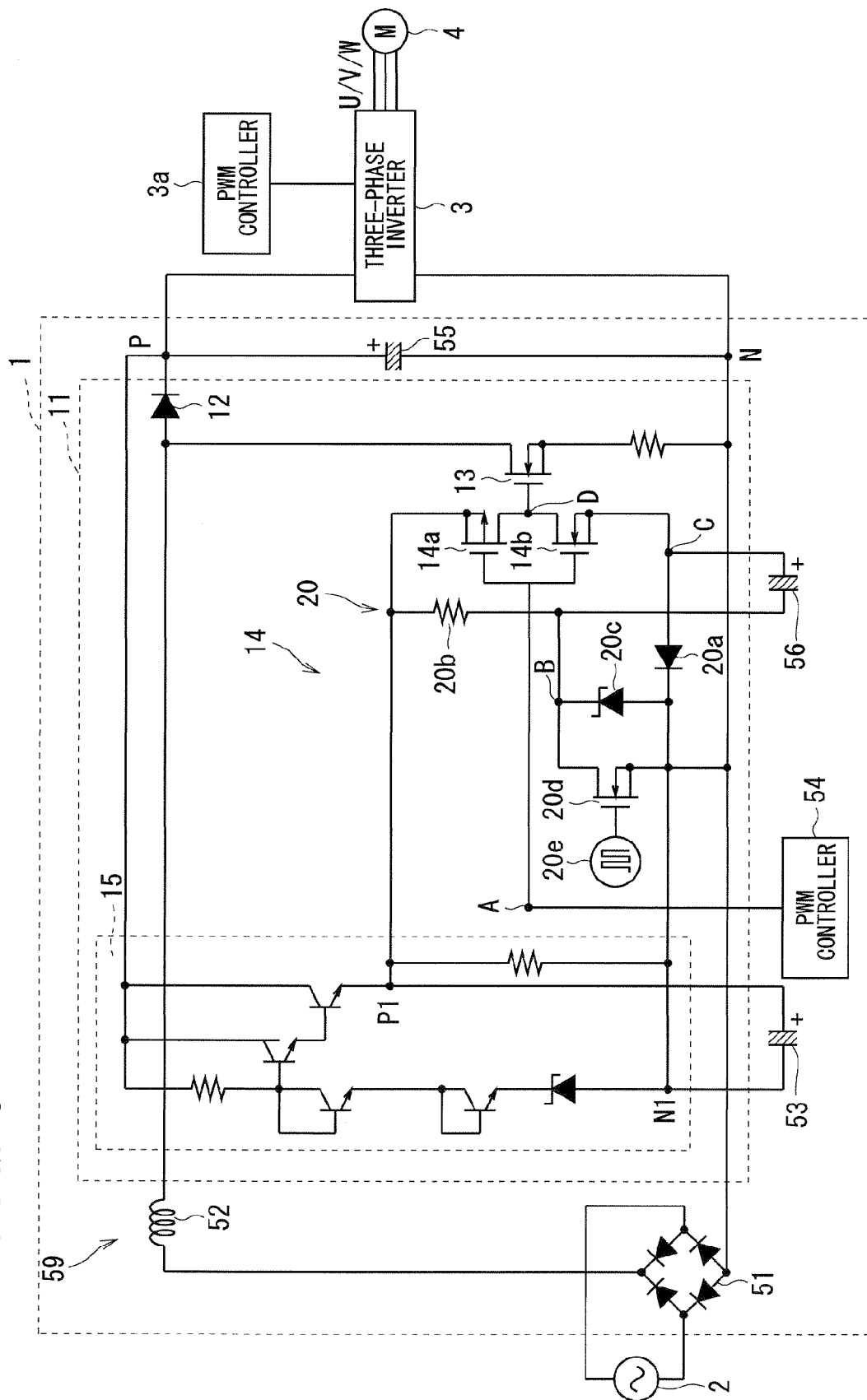
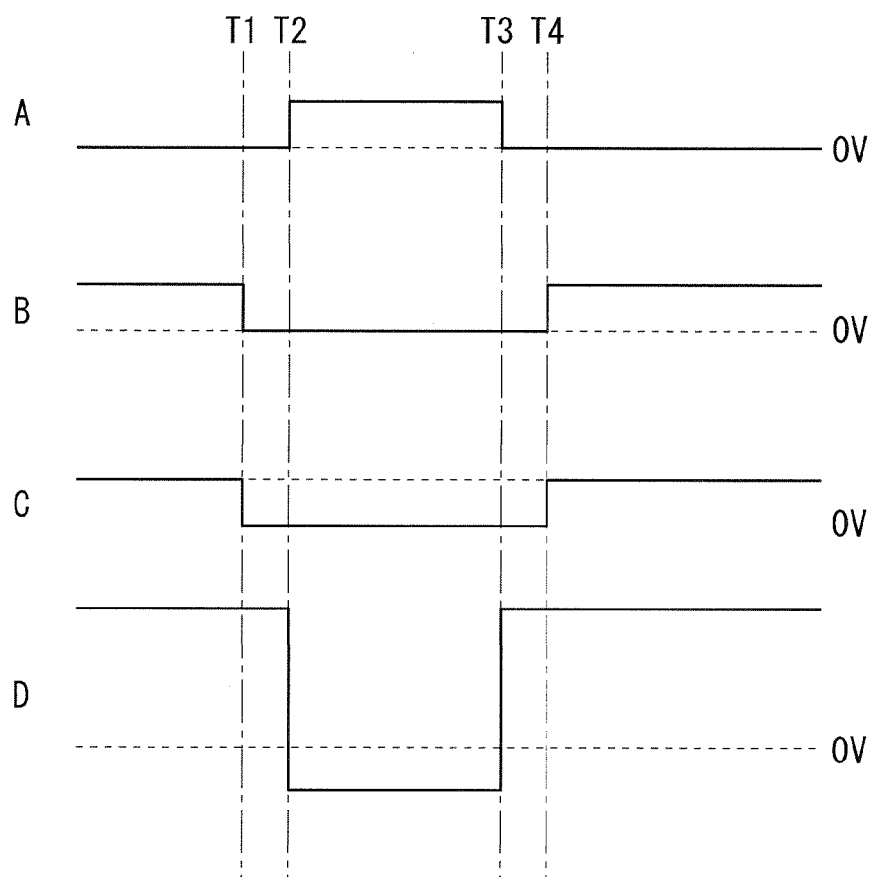




FIG. 7



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# SEMICONDUCTOR MODULE AND BOOST RECTIFIER CIRCUIT

## FIELD OF THE INVENTION

The present invention relates to a semiconductor module capable of generating a power source voltage to drive a boost converter, and a boost rectifier circuit including this semiconductor module.

## BACKGROUND ART

A boost converter, conventionally known as one of power semiconductor devices, boosts an input voltage to a desired voltage by using a semiconductor switching element such as an MOSFET (metal oxide semiconductor field effect transistor) and a driving IC (integrated circuit) that drives the semiconductor switching element. Generally, an AC voltage such as that supplied from a household AC power source or applied across an auxiliary winding is converted by a rectifier smoothing circuit composed of a diode, a capacitor and the like to a DC voltage, and the DC voltage is supplied to the boost converter as a power source voltage to drive the boost converter, as described for example in Japanese Patent Application Laid-Open Nos. 2012-74829 and 2006-53803, for example.

The power source voltage being obtained by rectifying the AC voltage and being supplied to the boost converter suffers from a problem such as its instability. Hence, in order to stabilize the power source voltage to drive the boost converter, an IC chip may be given a built-in linear regulator function capable of outputting a fixed voltage. However, a linear regulator circuit generally releases heat generated by a difference between an input voltage input to the linear regulator circuit and an output voltage output from the linear regulator circuit. Thus, a larger amount of heat is released in response to the increase of this difference.

This has made it difficult to provide an IC chip with a built-in linear regulator function that generates a power source voltage of about 15 V to drive the boost converter from a relatively high input voltage of about 100 V or more obtained by rectifying a commercial AC power source for example, in light of a problem such as temperature increase caused by heat generation by the linear regulator function.

## SUMMARY OF THE INVENTION

The present invention has been made in light of the aforementioned problems. It is an object of the present invention to provide a technique capable of suppressing temperature increase caused by a linear regulator function.

The present invention is directed to a semiconductor module including a voltage generator and a heat dissipating mechanism. The voltage generator is capable of generating, by using a built-in linear regulator function, a power source voltage to drive a boost converter based on a voltage boosted by the boost converter. The voltage generator is mounted on the heat dissipating mechanism.

The voltage generator having the built-in linear regulator function is mounted on the heat dissipating mechanism, so that temperature increase caused by the linear regulator function can be suppressed. Further, the power source voltage to drive the boost converter is generated by using the linear regulator function based on the voltage boosted by the boost converter, thereby achieving reduction of power consumption.

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These and other objects, features, aspects and advantages of the present invention will become more apparent from the following detailed description of the present invention when taken in conjunction with the accompanying drawings.

## BRIEF DESCRIPTION OF THE DRAWINGS

FIGS. 1 and 2 are circuit diagrams each showing the structure of a semiconductor module and that of a boost rectifier circuit according to a first preferred embodiment;

FIG. 3 is a sectional view showing the structure of the semiconductor module of the first preferred embodiment;

FIG. 4 is a circuit diagram showing the structure of a semiconductor module and that of a boost rectifier circuit according to a second preferred embodiment;

FIG. 5 is a timing chart showing the operation of the semiconductor module and that of the boost rectifier circuit of the second preferred embodiment;

FIG. 6 is a circuit diagram showing the structure of a semiconductor module and that of a boost rectifier circuit according to a third preferred embodiment; and

FIG. 7 is a timing chart showing the operation of the semiconductor module and that of the boost rectifier circuit of the third preferred embodiment.

## DESCRIPTION OF THE PREFERRED EMBODIMENTS

### First Preferred Embodiment

FIG. 1 is a circuit diagram showing the structure of a semiconductor module and that of a boost rectifier circuit including this semiconductor module, according to a first preferred embodiment of the present invention.

As described in detail later, a boost rectifier circuit 1 is capable of realizing a rectifying function of converting an AC voltage input from a commercial AC power source 2 to a DC voltage, and a boosting function of boosting this DC voltage. A three-phase inverter 3 converts the DC voltage boosted in the boost rectifier circuit 1 to an AC voltage and outputs the resultant AC voltage to a motor 4 under control of a PWM (pulse width modulation) controller 3a, thereby driving the motor 4.

The structure of the boost rectifier circuit 1 responsible for the aforementioned operation is described next. As shown in FIG. 1, the boost rectifier circuit 1 includes a semiconductor module 11, a diode bridge (rectifier circuit) 51, an inductor 52, a capacitor 53, a PWM controller 54, and a capacitor 55. While the capacitors 53 and 55 are described as being provided in the boost rectifier circuit 1, they may also be provided externally to the boost rectifier circuit 1.

The semiconductor module 11 is electrically connected to the diode bridge 51, the inductor 52, the capacitor 53, the PWM controller 54, and the capacitor 55. As shown in FIG. 1, the semiconductor module 11 includes a diode 12, a semiconductor switching element 13, a driving IC (driver) 14, and a voltage generator 15.

The diode 12 has a cathode connected at a point P to one end of the capacitor 55, and an anode connected to one end of the inductor 52.

The semiconductor switching element 13 has a source terminal connected at a point N to the opposite end of the capacitor 55, a drain terminal connected to the anode of the diode 12, and a gate terminal connected to the driving IC 14. In the first preferred embodiment, an MOSFET made of a wide band-gap semiconductor such as SiC or GaN is

employed as the semiconductor switching element **13**, thereby realizing higher breakdown voltage, size reduction, and higher switching speed.

The driving IC **14** transmits a voltage supplied to the driving IC **14** (here, power source voltage supplied from the voltage generator **15**) to the gate terminal of the semiconductor switching element **13** in response to a PWM signal (predetermined signal) input from the PWM controller **54**. If the driving IC **14** transmits (supplies) the voltage from the voltage generator **15** to the gate terminal of the semiconductor switching element **13** in response to the PWM signal, the semiconductor switching element **13** is ON. If the driving IC **14** does not transmit (supply) the voltage from the voltage generator **15** to the gate terminal of the semiconductor switching element **13** in response to the PWM signal, the semiconductor switching element **13** is OFF. To be specific, the driving IC **14** is configured so as to drive the semiconductor switching element **13** in response to the PWM signal.

The rectifying and boosting functions of the boost rectifier circuit **1** are described next before description of the voltage generator **15**.

#### <Rectifying Function>

The diode bridge **51** is connected to the semiconductor module **11** (here, the source terminal of the semiconductor switching element **13**) and the inductor **52**. The diode bridge **51** outputs a waveform with positive polarity as it is of an AC voltage input from the commercial AC power source **2**, and converts a waveform with negative polarity of this AC voltage to a waveform with positive polarity and outputs the resultant waveform, thereby converting the AC voltage to a DC voltage.

#### <Boosting Function>

The boost rectifier circuit **1** includes a boost converter **59** that boosts the DC voltage converted by the diode bridge **51**. The boost converter **59** includes the diode **12**, the semiconductor switching element **13**, the inductor **52**, and the capacitor **55**.

More specifically, in response to switching of the semiconductor switching element **13** from OFF to ON, a DC current resulting from the DC voltage from the diode bridge **51** flows into the inductor **52** to accumulate energy in the inductor **52**. In response to switching of the semiconductor switching element **13** from ON to OFF, a DC voltage responsive to the energy accumulated in the inductor **52** is stored in the capacitor **55** via the diode **12**. If the semiconductor switching element **13** is switched from OFF to ON again thereafter, the rectifying function of the diode **12** suppresses discharge of the capacitor **55**.

As a result, a DC voltage across the terminals of the capacitor **55** (across the points P and N) is increased each time the semiconductor switching element **13** is switched between ON and OFF. This voltage increase can be controlled based on a duty ratio between ON and OFF of the semiconductor switching element **13**, specifically, a duty ratio of the PWM signal. This allows the boost converter **59** to boost the DC voltage converted by the diode bridge **51** to a desired voltage based on the duty ratio of the PWM signal.

#### <Voltage Generator>

The voltage generator **15** is described next. The voltage generator **15** is capable of generating, by using a built-in linear regulator function, a power source voltage to drive the boost converter **59** (voltage to be supplied to the driving IC **14**) based on a voltage across the points P and N boosted by the boost converter **59** (hereinafter also called a “boosted voltage” in some cases). In the first preferred embodiment, the voltage generator **15** and the capacitor **53** form a linear

regulator circuit that generates the power source voltage based on the boosted voltage.

FIG. 2 shows the linear regulator circuit composed of the voltage generator **15** and the capacitor **53**.

The voltage generator **15** includes a resistor **15a**, a plurality of transistors **15b**, a Zener diode **15c**, a transistor **15d**, a transistor **15e**, and a resistor **15f**. The point P, the resistor **15a**, the transistors **15b**, the Zener diode **15c**, and the point N are connected in series in this order. The transistor **15d** has a base terminal connected to a node between the resistor **15a** and the transistor **15b** at the top in the plane of the drawing, and a collector terminal connected to the point P. The transistor **15e** is connected to the transistor **15d** in a Darlington configuration. The resistor **15f** is interposed between the emitter terminal of the transistor **15e** and a ground potential.

The capacitor **53** is connected in parallel with the resistor **15f** and the driving IC **14** between a point P1 (node between the transistor **15e** and the resistor **15f**) and a point N1 (ground potential).

Even if a voltage supplied across the points P and N fluctuates to some degree, the linear regulator circuit of the aforementioned structure outputs a fixed voltage lower than the voltage across the points P and N to the driving IC **14** interposed between the points P1 and N1. Referring to the example of FIG. 2, assuming that the voltage across the points P and N is from about 200 V to about 370 V, the linear regulator circuit generates a fixed voltage between the points P1 and N1, substantially same as a power source voltage supplied to the driving IC **14** (15 V, for example). In this structure, assuming that the driving IC **14** has an impedance of 3 k $\Omega$ , a total loss generated in the linear regulator circuit becomes about 3.3 W.

The linear regulator circuit releases heat generated by a difference between an input voltage input to the linear regulator circuit and an output voltage output from the linear regulator circuit. This makes it difficult to provide the semiconductor module **11** with a built-in linear regulator function, specifically the voltage generator **15**, in light of a problem such as temperature increase. In contrast, the semiconductor module **11** of the first preferred embodiment is capable of suppressing temperature increase caused by the linear regulator function.

FIG. 3 is a sectional view showing the structure of the semiconductor module of the first preferred embodiment. The semiconductor module **11** includes a heat dissipating mechanism (insulating heat dissipating sheet **16** and heat sink **17**), metal frames (first metal frame **18a** and second metal frame **18b**), and a resin mold **19**, in addition to the diode **12**, the semiconductor switching element **13**, the driving IC **14**, and the voltage generator **15** described above.

The insulating heat dissipating sheet **16** is formed on the heat sink **17** so as to contact the heat sink **17** tightly. The first and second metal frames **18a** and **18b** are formed on the insulating heat dissipating sheet **16** so as to contact the insulating heat dissipating sheet **16** tightly. The first and second metal frames **18a** and **18b** are composed of copper frames, for example. The diode **12** and the semiconductor switching element **13** are formed on the first metal frame **18a**. The driving IC **14** and the voltage generator **15** are formed on the second metal frame **18b**. To be specific, in the first preferred embodiment, the voltage generator **15** is mounted on the heat dissipating mechanism (insulating heat dissipating sheet **16** and heat sink **17**).

The diode **12** and the semiconductor switching element **13**, the driving IC **14** and the voltage generator **15**, and the first and second metal frames **18a** and **18b** (package pins),

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are connected to each other appropriately via metal wires (not shown in the drawings) made of silver, aluminum and copper, for example. While not shown in the drawings, components such as the inductor **52** and the capacitors **53** and **55** are connected to the first and second metal frames **18a** and **18b** (package pins) outside the resin mold **19**.

The resin mold **19** covers the components of the semiconductor module **11**, except respective terminal portions of the first and second metal frames **18a** and **18b** and a surface of the heat sink **17** opposite a surface thereof on which the insulating heat dissipating sheet **16** is arranged. The resin mold **19** may be made of an epoxy resin, for example.

A semiconductor module without the aforementioned heat dissipating mechanism has a relatively high heat resistance. A temperature was estimated under operating condition of the linear regulator function of the voltage generator **15** while assuming a heat resistance to be 100° C./W, for example, and was found to increase to about 330° C. Such a semiconductor module suffers from a problem such as strict limitations on the temperature of environment where this semiconductor module is used, so that it cannot be provided with the voltage generator **15** therein.

In contrast, the semiconductor module **11** of the first preferred embodiment includes the aforementioned heat dissipating mechanism, allowing reduction of a heat resistance. A temperature was estimated under operating condition of the linear regulator function of the voltage generator **15** while assuming a heat resistance to be 3.5° C./W, for example, and was found to be about 11.6° C. Accordingly, it was found that the semiconductor module **11** can reduce temperature, compared to the semiconductor module without the aforementioned heat dissipating mechanism.

As described above, according to the semiconductor module **11** and the boost rectifier circuit **1** of the first preferred embodiment, the voltage generator **15** having the built-in linear regulator function is mounted on the heat dissipating mechanism. This can suppress temperature increase caused by the linear regulator function. Further, a power source voltage to drive the boost converter **59** is generated by using the linear regulator function based on a voltage boosted by the boost converter **59**, thereby allowing reduction of power consumption (power to be supplied from outside).

#### Second Preferred Embodiment

FIG. **4** is a circuit diagram showing the structure of a semiconductor module and that of a boost rectifier circuit according to a second preferred embodiment of the present invention. Components of the semiconductor module and those of the boost rectifier circuit of the second preferred embodiment same as or similar to those described in the first preferred embodiment are identified by the same reference numbers, and differences from the first preferred embodiment are mainly described below.

FIG. **4** shows a specific circuit example of the driving IC **14**, and a voltage supply **20** and a capacitor **56** are added in FIG. **4**. While the capacitor **56** is described as being provided externally to the voltage supply **20**, it may also be provided in the voltage supply **20**.

The driving IC **14** shown in FIG. **4** includes a semiconductor switching element **14a** and a semiconductor switching element **14b**. The voltage supply **20** includes a diode **20a**, a resistor **20b**, a Zener diode **20c**, and a semiconductor switching element **20d**. The semiconductor switching element **14a** is composed of a P-type MOSFET, and the semiconductor switching elements **14b** and **20d** are each composed of an N-type MOSFET.

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The point **P1**, the semiconductor switching elements **14a** and **14b**, the diode **20a**, and the point **N1** are connected in series in this order. A node between the respective drain terminals of the semiconductor switching elements **14a** and **14b** is connected to the gate terminal of the semiconductor switching element **13**. The respective gate terminals of the semiconductor switching elements **14a** and **14b** receive a PWM signal given from the PWM controller **54**. The diode **20a** has an anode connected to the source terminal of the semiconductor switching element **14b**, and a cathode connected to the point **N1**.

The source terminal of the semiconductor switching element **14a**, the resistor **20b**, the capacitor **56**, and the source terminal of the semiconductor switching element **14b** are connected in series in this order. The Zener diode **20c** has a cathode connected to a node between the resistor **20b** and the capacitor **56**, and an anode connected to the cathode of the diode **20a**. The semiconductor switching element **20d** has a gate terminal connected to the respective gate terminals of the semiconductor switching elements **14a** and **14b**, a drain terminal connected to the cathode of the Zener diode **20c**, and a source terminal connected to the anode of the Zener diode **20c**.

FIG. **5** is a timing chart showing operations in the semiconductor module and the boost rectifier circuit of the aforementioned structures of the second preferred embodiment during switching between ON and OFF of the semiconductor switching element **13**. Symbols A, B, C, and D of FIG. **5** correspond to points A, B, C, and D of FIG. **4** respectively.

A control signal (PWM signal from PWM controller **54**) to turn ON or OFF the semiconductor switching element **13** is applied to the point A.

At the time of turn-on, a potential at the point A is switched from H to L. In response, the semiconductor switching element **14a** becomes ON (active) whereas the semiconductor switching elements **14b** and **20d** become OFF (passive). Thus, a potential at the point D becomes the same as a power source voltage (15 V, for example) supplied from the voltage generator **15**, thereby turning on the semiconductor switching element **13**. Further, a current flows from the voltage generator **15** into the resistor **20b** and the Zener diode **20c**. In response, a potential at the point B is increased by a voltage  $V_F$  (5 V, for example) of the Zener diode **20c**, and electric charge corresponding to this voltage (5 V, for example) is stored in the capacitor **56**.

At the time of turn-off, the potential at the point A is switched from L to H. In response, the semiconductor switching element **14a** becomes OFF (passive) whereas the semiconductor switching elements **14b** and **20d** become ON (active). Thus, the potential at the point B becomes the same as a potential at the point N (here, 0 V) and the respective potentials at the points C and D also become substantially the same as the potential at the point N, thereby turning off the semiconductor switching element **13**. Meanwhile, as a result of the function of a charge pump system using the voltage of the capacitor **56**, the potential at the point C is reduced, compared to the potential at the point N, to a negative value by a voltage (5 V, for example) stored in the capacitor **56**. The potential at the point D is also reduced by the same amount to a negative value for the same reason.

As described above, in the second preferred embodiment, the voltage supply **20** is capable of supplying a negative bias to the semiconductor switching element **13** during a non-transmission period (predetermined period) where the driving IC **14** does not transmit a power source voltage of the driving IC **14** to the semiconductor switching element **13**.

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This prevents a voltage applied to the gate terminal of the semiconductor switching element **13** from exceeding a threshold voltage, even if this gate terminal receives large noise and the like while the semiconductor switching element **13** is OFF. More specifically, noise tolerance of the semiconductor switching element **13** is enhanced to realize stable switching control.

This works effectively, especially if the semiconductor switching element **13** is composed of an element having a relatively low threshold voltage such as an MOSFET made of a wide band-gap semiconductor such as SiC or GaN.

### Third Preferred Embodiment

FIG. **6** is a circuit diagram showing the structure of a semiconductor module and that of a boost rectifier circuit according to a third preferred embodiment of the present invention. Components of the semiconductor module and those of the boost rectifier circuit of the third preferred embodiment same as or similar to those described in the second preferred embodiment are identified by the same reference numbers, and differences from the second preferred embodiment are mainly described below.

In the aforementioned second preferred embodiment (FIG. **4**), the PWM signal is input to the gate terminal of the semiconductor switching element **20d**, and timing of switching of the semiconductor switching element **13** to the non-transmission period (OFF period) is synchronous with timing of switching of the semiconductor switching element **20d** to ON period.

In the third preferred embodiment, the voltage supply **20** additionally includes a signal oscillator **20e**. The signal oscillator **20e** is configured so as to input a square wave signal to the gate terminal of the semiconductor switching element **20d**. This square wave signal makes the timing of switching of the semiconductor switching element **13** to OFF period (non-transmission period) asynchronous with the timing of the semiconductor switching element **20d** to ON period.

FIG. **7** is a timing chart showing operations in the semiconductor module and the boost rectifier circuit of the aforementioned structures of the third preferred embodiment during switching between ON and OFF of the semiconductor switching element **13**. Symbols A, B, C, and D of FIG. **7** correspond to points A, B, C, and D of FIG. **6** respectively.

In the third preferred embodiment, at time **T1** before time **T2** when a potential at the point A is switched from L to H, the signal oscillator **20e** inputs a square wave signal switching from L to H to the semiconductor switching element. Further, at time **T4** after time **T3** when the potential at the point A is switched from H to L, the signal oscillator **20e** inputs a square wave signal switching from H to L to the semiconductor switching element **20d**. The operation of the semiconductor module and that of the boost rectifier circuit of the third preferred embodiment at each of the times **T1** to **T4** are described in detail next.

At the time **T1**, the potential at the point A is maintained L. Thus, the semiconductor switching elements **14a** and **14b** are maintained ON and OFF respectively. Meanwhile, the gate terminal of the semiconductor switching element **20d** is switched from L to H, thereby switching the semiconductor switching element **20d** from OFF to ON. This makes a potential at the point B become the same as a potential at the point N, and reduces a potential at the point C, compared to the potential at the point N, to a negative value by a voltage (5 V, for example) stored in the capacitor **56** as a result of the function of a charge pump system. Meanwhile, the semi-

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conductor switching elements **14a** and **14b** are ON and OFF respectively. Thus, a potential at the point D is maintained not at the potential of the point C but at a power source voltage (15 V, for example) supplied from the voltage generator **15**, so that the semiconductor switching element **13** is maintained ON.

At the time **T2**, the potential at the point A is switched from L to H. This switches the semiconductor switching elements **14a** and **14b** from ON to OFF and from OFF to ON respectively. Thus, the potential at the point D deviates from the aforementioned power source voltage and becomes the same as the potential at the point C, thereby turning OFF the semiconductor switching element **13**.

At the time **T3**, the potential at the point A is switched from H to L. This switches the semiconductor switching elements **14a** and **14b** from OFF to ON and from ON to OFF respectively. Thus, the potential at the point D deviates from the potential at the point C and becomes the same as the aforementioned power source voltage, thereby turning ON the semiconductor switching element **13**.

At the time **T4**, the potential at the point A is maintained L, so that the semiconductor switching elements **14a** and **14b** are maintained ON and OFF respectively. Meanwhile, the gate terminal of the semiconductor switching element **20d** is switched from H to L, thereby switching the semiconductor switching element **20d** from ON to OFF. Then, a current flows from the voltage generator **15** into the resistor **20b** and the Zener diode **20c**. In response, the potential at the point B is increased by a voltage **VF** (5 V, for example) of the Zener diode **20c**, and electric charge corresponding to this voltage (5 V, for example) is stored in the capacitor **56**. At the same time, the potential at the point C becomes 0 V.

According to the semiconductor module **11** and the boost rectifier circuit **1** of the third preferred embodiment described above, a negative bias can be supplied to the semiconductor switching element **13** during a period between the times **T1** and **T4** longer than a non-transmission period between the times **T2** and **T3** where a power source voltage is not transmitted from the driving IC **14** to the semiconductor switching element **13**. This makes it possible to supply a negative bias without delay in the non-transmission period between the times **T2** and **T3** (OFF period of the semiconductor switching element **13**), realizing stable switching control reliably.

The preferred embodiments of the present invention can be combined freely, and each of the preferred embodiments can be modified or omitted where appropriate without departing from the scope of the invention.

While the invention has been shown and described in detail, the foregoing description is in all aspects illustrative and not restrictive. It is therefore understood that numerous modifications and variations can be devised without departing from the scope of the invention.

What is claimed is:

1. A semiconductor module, comprising
  - a voltage generator capable of generating, by using a built-in linear regulator function, a power source voltage to drive a boost converter based on a voltage boosted by said boost converter,
  - a driver that drives said boost converter,
  - a heat dissipating mechanism on which said voltage generator is mounted,
  - a semiconductor switching element being part of said boost converter, and
  - a voltage supply capable of supplying a negative bias to said semiconductor switching element during a predetermined period including a non-transmission period

where said driver does not transmit said power source voltage to said semiconductor switching element, wherein power from an output of said driver is provided to an input of said voltage generator, wherein said driver drives said semiconductor switching element by transmitting said power source voltage to said semiconductor switching element in response to a predetermined signal, and wherein said voltage supply comprises a diode, a resistor, a Zener diode and a semiconductor switching device between said driver and said voltage generator.

2. The semiconductor module according to claim 1, wherein said predetermined period is longer than said non-transmission period.

3. The semiconductor module according to claim 1, wherein said semiconductor switching element is made of a material including a wide band-gap semiconductor.

4. A boost rectifier circuit, comprising:  
the semiconductor module as recited in claim 1;  
an inductor being part of said boost converter; and  
a rectifier circuit connected to said semiconductor module and said inductor.

5. The semiconductor module according to claim 1, wherein said voltage generator, said boost converter and said driver are mounted on said heat dissipating mechanism.

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